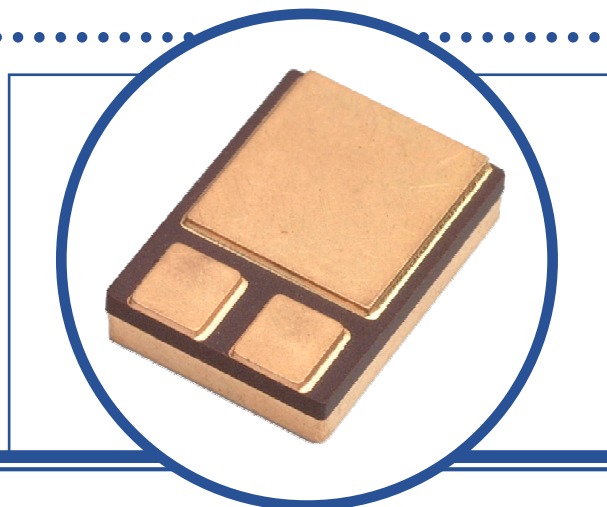


SILICON CARBIDE (SiC) SCHOTTKY DIODE

SML10SiC06SMD

- Hermetic Ceramic Surface Mount Package.
- Semelab's Silicon Carbide (SiC) Schottky diodes exhibit low forward voltage and superb high temperature performance.
- Suitable for high-frequency hard switching applications, where system efficiency and reliability are paramount.
- No reverse recovery time due to absence of minority carrier injection.
- Screening Options Available.



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

V_R	DC Reverse Voltage	600V
V_{RRM}	Repetitive Peak Reverse Voltage	600V
I_F	DC Forward Current ($T_J = 175^\circ\text{C}$)	10A
I_{FRM}	Repetitive Peak Forward Current ⁽¹⁾	67A
I_{FSM}	Surge Peak Forward Current ⁽²⁾	250A
P_D	Total Power Dissipation at Derate Above 25°C	100W 0.5W/ $^\circ\text{C}$
T_J	Junction Temperature Range	-55 to $+225^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to $+225^\circ\text{C}$

THERMAL PROPERTIES

Symbols	Parameters	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction To Case	2.0	$^\circ\text{C/W}$

Notes

(1) $T_c = 25^\circ\text{C}$, $T_p = 10\text{ms}$, Half Sine Wave, $D = 0.3$

(2) $T_c = 25^\circ\text{C}$, $T_p = 10\mu\text{s}$

SILICON CARBIDE (SiC) SCHOTTKY DIODE SML10SIC06SMD

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise stated)

Static Characteristics

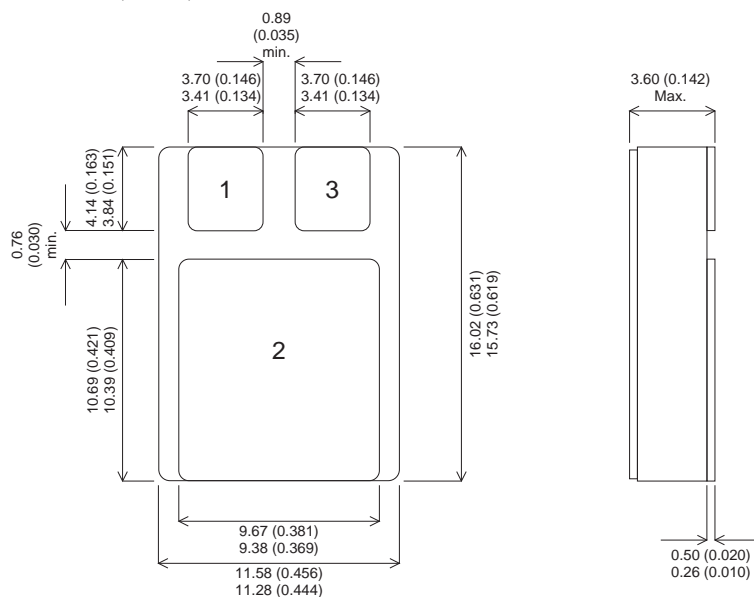
Symbols	Parameters	Test Conditions	Min.	Typ.	Max.	Units
V _F	Forward Voltage	I _F = 10A		1.5	1.8	V
		T _J = 175°C		2.0	2.4	
I _R	Reverse Current	V _R = 600V		10	50	μA
		T _J = 175°C		20	200	

Dynamic Characteristics

Q _C	Total Capacitive Charge	V _R = 600V, I _F = 10A di/dt = 500A/μs		25		nC
C	Total Capacitance	V _R = 1.0V, f = 1.0MHz		480		pF
		V _R = 200V, f = 1.0MHz		50		
		V _R = 400V, f = 1.0MHz		42		

MECHANICAL DATA

Dimensions in mm (inches)



SMD1 (TO-276AB)

Underside View

Pad 1 – Anode Pad 2 – Cathode Pad 3 – Anode

